



Unimap

BST CAPACITOR THIN FILMS

INVENTORS

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INTRODUCTION

Ferroelectric $Ba_{0.5}Sr_{0.5}TiO_3$ (BST) thin films are well known as dielectric materials. They have been used as capacitors and high density dynamic random access memory (DRAM) due to their high dielectric constant and high capacity of charge storage and ferroelectric device.

PRODUCT FABRICATION & CHARACTERIZATION:

Fabrication process is simple:

- Preparation of silicon substrate and BST solution
- Masking
- Spin Coating
- Heating
- Masking
- Metal contact
- CV Measurement

PRODUCT NOVELTIES

- Fabrication process is relatively simple and readily available
- Fabricated on silicon hence miniaturization & integration with integrated circuit are possible

wire

